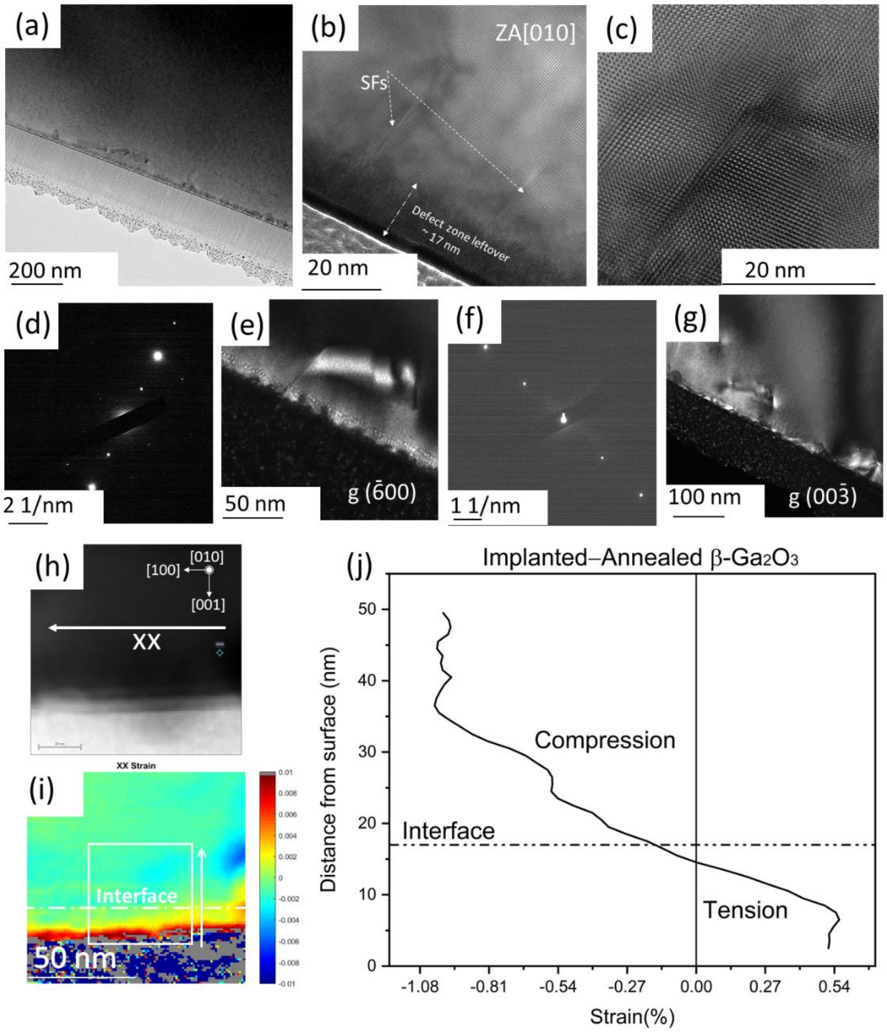

Figure 1[5]. Cross-sectional TEM image of the uppermost region implanted-annealed epi layer (a) and HRTEM images showing the presence of SFs (b) and (c). Two beam condition images along the [010] zone axis (d) and (f) and corresponding weak beam images obtained from g (600) (e) and g(003) (g). Virtual bright field STEM image of implanted-annealed b-Ga2O3 (h) and corresponding strain mapping/profile (i) and (j).

References:

1. Yang, et al., Appl. Phys. Lett. 114, 232106 (2019); https://doi.org/10.1063/1.5100256
2. Sharma , et al., Journal of Vacuum Science & Technology B 37, 051204 (2019); https://doi.org/10.1116/1.5118001
3. Yamaguchi, et al , *J. Appl. Crystallogr.* **51**, 1372–1377, (2018).
4. Kim, *et al*, *J. Mater. Chem. C* **7**, 10–24 (2018).
5. Anber et al., Appl. Phys. Lett. 117, 152101 (2020); https://doi.org/10.1063/5.0022170